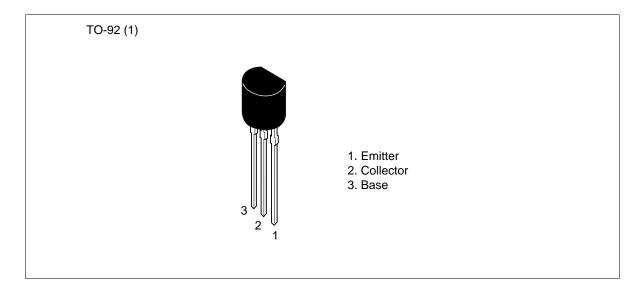
Silicon PNP Epitaxial

HITACHI

Application

- Low frequency low noise amplifier
- Complementary pair with 2SC2545, 2SC2546 and 2SC2547

Outline





Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

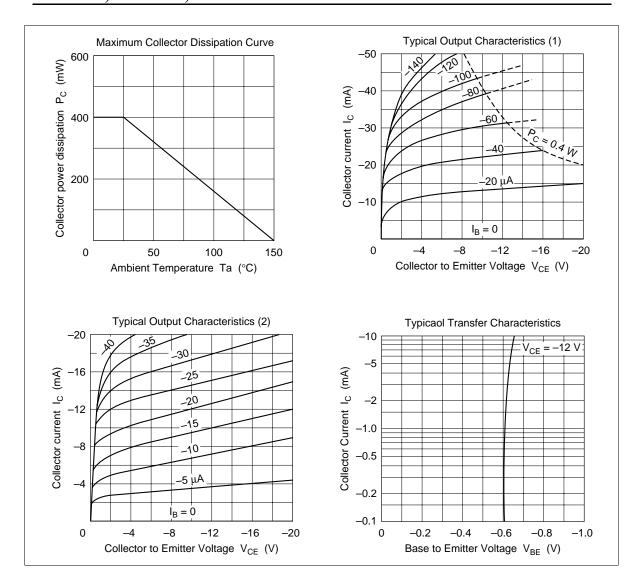
Item	Symbol	2SA1083	2SA1084	2SA1085	Unit
Collector to base voltage	V_{CBO}	-60	-90	-120	V
Collector to emitter voltage	V _{CEO}	-60	-90	-120	V
Emitter to base voltage	V_{EBO}	- 5	- 5	- 5	V
Collector current	I _c	-100	-100	-100	mA
Emitter current	I _E	100	100	100	mA
Collector power dissipation	P_{c}	400	400	400	mW
Junction temperature	Tj	150	150	150	°C
Storage temperature	Tstg	-55 to +150	-55 to +150	-55 to +150	°C

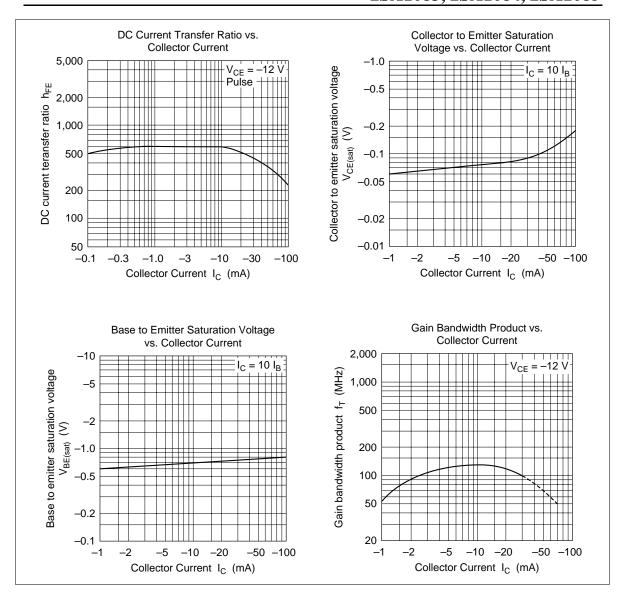
Electrical Characteristics ($Ta = 25^{\circ}C$)

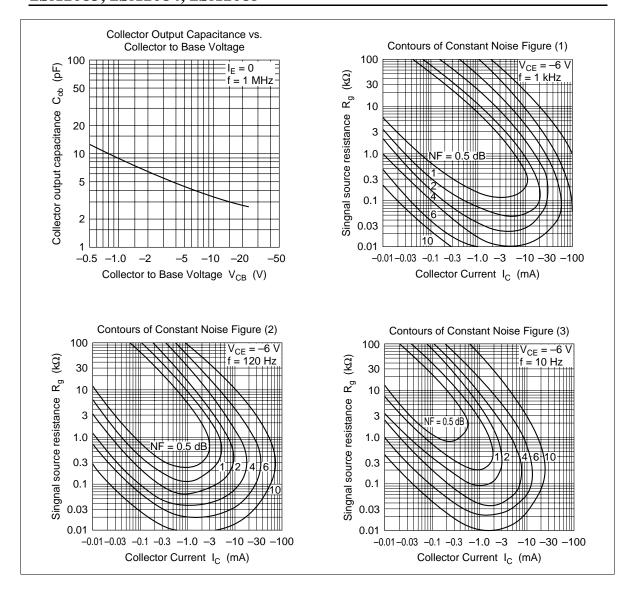
		2SA1	083		2SA1084		2SA1085					
Item	Symbol	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	-60	_	_	-90	_	_	-120	_	_	V	$I_{C} = -10 \mu\text{A}, I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-60	_	_	-90	_	_	-120	_	_	V	$I_{C} = -1 \text{ mA},$ $R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	- 5	_	_	- 5	_	_	- 5	_	_	V	$I_E = -10 \mu A, I_C = 0$
Collector cutoff current	I _{CBO}	_	_	-0.1	_	_	-0.1	_	_	-0.1	μΑ	$V_{CB} = -50 \text{ V}, I_{E} = 0$
Emitter cutoff current	I_{EBO}	_	_	-0.1	_	_	-0.1	_	_	-0.1	μΑ	$V_{EB} = -2 \text{ V}, I_{C} = 0$
DC current transfer ratio	h _{FE} *1	250	_	800	250	_	800	250	_	800		$V_{CE} = -12 \text{ V},$ $I_{C} = -2 \text{ mA}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	-0.2	_	_	-0.2	_	_	-0.2	V	$I_C = -10 \text{ mA},$ $I_B = -1 \text{ mA}$
Base to emitter voltage	V_{BE}	_	-0.6	-	_	-0.6	-	_	-0.6	-	V	$V_{CE} = -12 \text{ V},$ $I_{C} = -2 \text{ mA}$
Gain bandwidth product	f _T	_	90	_	_	90	_	_	90	_	MHz	$V_{CE} = -12 \text{ V},$ $I_{C} = -2 \text{ mA}$
Collector output capacitance	Cob	_	3.5	_	_	3.5	_	_	3.5	_	pF	$V_{CB} = -10 \text{ V}, I_{E} = 0,$ f = 1 MHz
Noise voltage reffered to input	e _n	_	0.5	_	_	0.5	_	_	0.5	_	nV/ √Hz	$V_{CE} = -6V,$ $I_{C} = -10 \text{ mA},$ $f = 1 \text{ kHz},$ $R_{g} = 0, \Delta f = 1 \text{Hz}$

Note: 1. The 2SA1083, 2SA1084 and 2SA1085 are grouped by h_{FE} as follows.

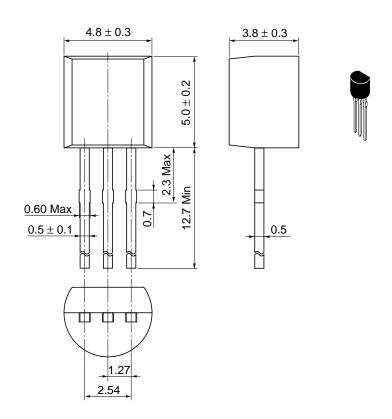
D	E
250 to 500	400 to 800







Unit: mm



Hitachi Code	TO-92 (1)
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.25 g

Cautions

- 1. Hitachi neither warrants nor grants licenses of any rights of Hitachi's or any third party's patent, copyright, trademark, or other intellectual property rights for information contained in this document. Hitachi bears no responsibility for problems that may arise with third party's rights, including intellectual property rights, in connection with use of the information contained in this document.
- 2. Products and product specifications may be subject to change without notice. Confirm that you have received the latest product standards or specifications before final design, purchase or use.
- 3. Hitachi makes every attempt to ensure that its products are of high quality and reliability. However, contact Hitachi's sales office before using the product in an application that demands especially high quality and reliability or where its failure or malfunction may directly threaten human life or cause risk of bodily injury, such as aerospace, aeronautics, nuclear power, combustion control, transportation, traffic, safety equipment or medical equipment for life support.
- 4. Design your application so that the product is used within the ranges guaranteed by Hitachi particularly for maximum rating, operating supply voltage range, heat radiation characteristics, installation conditions and other characteristics. Hitachi bears no responsibility for failure or damage when used beyond the guaranteed ranges. Even within the guaranteed ranges, consider normally foreseeable failure rates or failure modes in semiconductor devices and employ systemic measures such as failsafes, so that the equipment incorporating Hitachi product does not cause bodily injury, fire or other consequential damage due to operation of the Hitachi product.
- 5. This product is not designed to be radiation resistant.
- 6. No one is permitted to reproduce or duplicate, in any form, the whole or part of this document without written approval from Hitachi.
- 7. Contact Hitachi's sales office for any questions regarding this document or Hitachi semiconductor products.

IITACH

Semiconductor & Integrated Circuits.

Nippon Bldg., 2-6-2, Öhte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

NorthAmerica http:semiconductor.hitachi.com/ Europe http://www.hitachi-eu.com/hel/ecg

Asia (Singapore) Asia (Taiwan) Asia (HongKong) http://www.has.hitachi.com.sg/grp3/sicd/index.htm http://www.hitachi.com.tw/E/Product/SICD_Frame.htm http://www.hitachi.com.hk/eng/bo/grp3/index.htm

Japan http://www.hitachi.co.jp/Sicd/indx.htm

For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive. San Jose, CA 95134 Tel: <1> (408) 433-1990 Fax: <1>(408) 433-0223

Hitachi Europe GmbH Electronic components Group D-85622 Feldkirchen, Munich Germany

Tel: <49> (89) 9 9180-0 Fax: <49> (89) 9 29 30 00 Hitachi Europe Ltd.

Electronic Components Group. Whitebrook Park Lower Cookham Road Maidenhead

Berkshire SL6 8YA, United Kingdom Tel: <44> (1628) 585000 Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd. 16 Collyer Quay #20-00 Hitachi Tower Singapore 049318 Tel: 535-2100 Fax: 535-1533

Hitachi Asia Ltd. Taipei Branch Office 3F, Hung Kuo Building. No.167, Tun-Hwa North Road, Taipei (105) Tel: <886> (2) 2718-3666 Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd. Group III (Electronic Components) 7/F., North Tower, World Finance Centre, Harbour City, Canton Road, Tsim Sha Tsui, Kowloon, Hong Kong Tel: <852> (2) 735 9218 Fax: <852> (2) 730 0281

Telex: 40815 HITEC HX

Copyright ' Hitachi, Ltd., 1999. All rights reserved. Printed in Japan.